

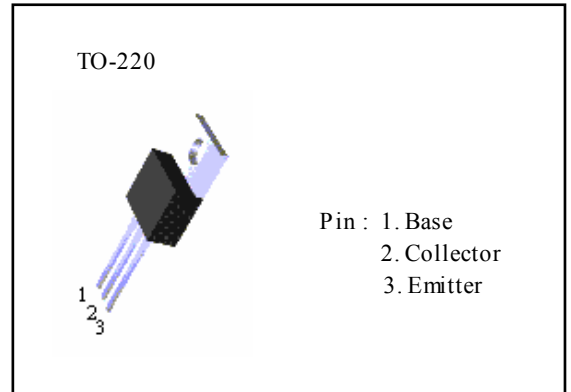
PNP Epitaxial Silicon Darlington Transistor

MEDIUM POWER LINEAR SWITCHING APPLICATIONS

- Collector current 18A
- Collector dissipation $P_c = 100W$ ($T_c = 25^\circ C$)

ORDERING INFORMATION

Device	Operating Temperature	Package
PJP168ACZ	$-20^\circ C \sim +85^\circ C$	TO-220



ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

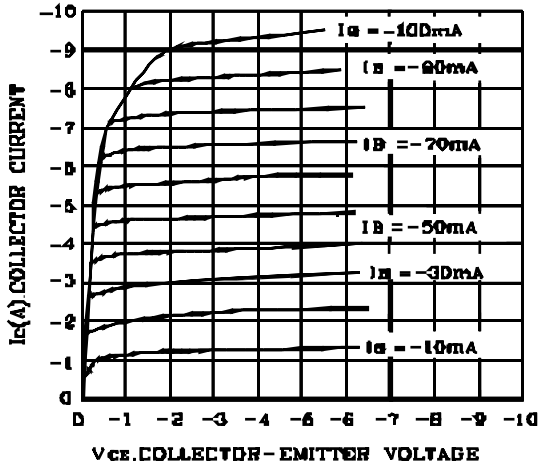
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-13	V
Emitter-Base Voltage	V_{EBO}	-7	V
Collector Current	I_c	-18	A
Collector Dissipation	P_c	100	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	$-55 \sim 150$	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

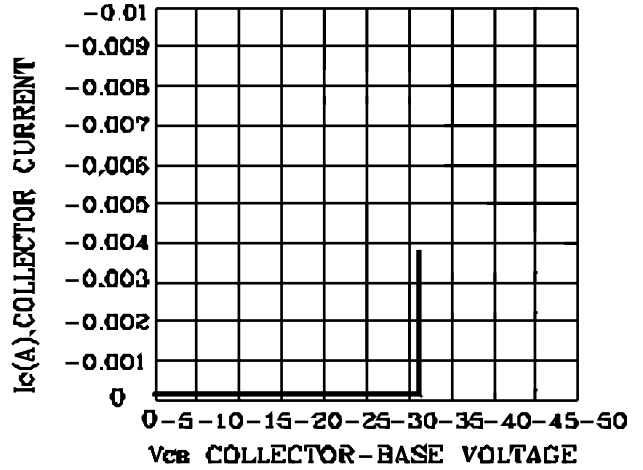
Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c = -1mA, I_E = 0$	-20			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c = -10mA, I_B = 0$	-13			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -1mA, I_C = 0$	-7			V
Collector Cutoff Current	I_{CBO}	$V_{CB} = -15V, I_E = 0$			-100	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -3V, I_C = 0$			-100	μA
DC Current Gain	h_{FE1}	$V_{CE} = -3V, I_C = -10A$	120			
	h_{FE2}	$V_{CE} = -3V, I_C = -15A$	90			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -10A, I_B = -1A$			-0.7	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = -10A, V_{CE} = -4V$			-1.5	V

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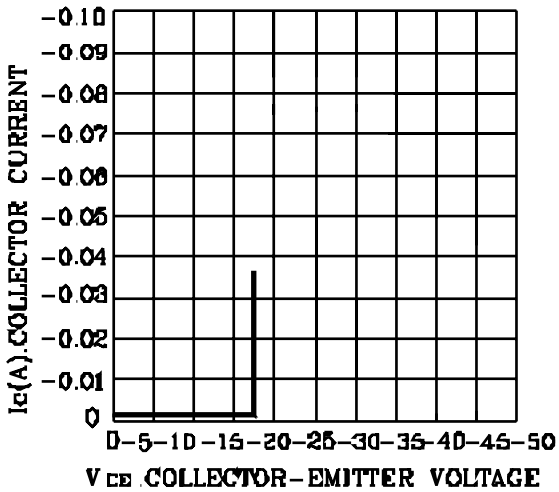
DC CURRENT GAIN



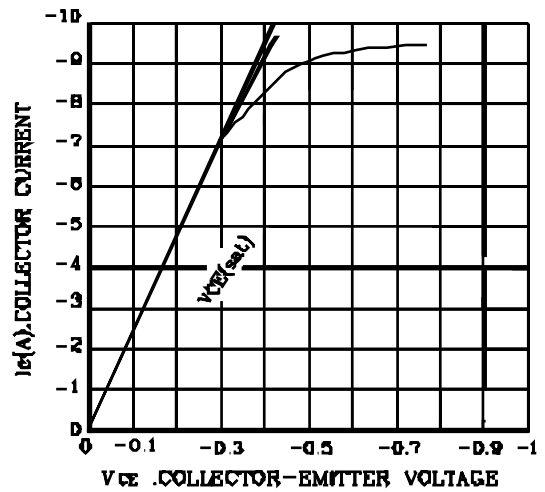
COLLECTOR-BASE BREAKDOWN VOLTAGE



COLLECTOR-EMITTER BREAKDOWN VOLTAGE



COLLECTOR-EMITTER SATURATION VOLTAGE



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TO-220 Unit:mm

